

FS5UM-10

HIGH-SPEED SWITCHING USE

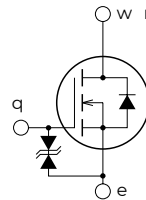
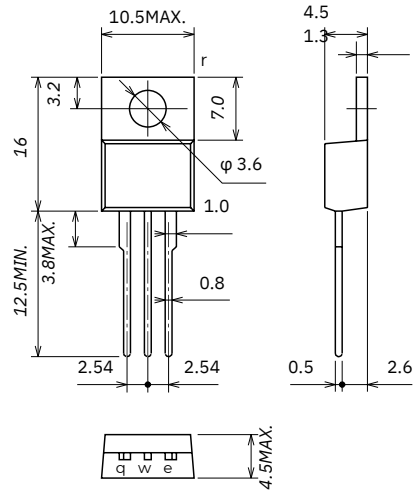
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V_{DSS}	500V
$r_{DS(ON)}$ (MAX).....	1.8Ω
I_D	5A

OUTLINE DRAWING

Dimensions in mm



q GATE
w DRAIN
e SOURCE
r DRAIN

TO-220

APPLICATION

SMPS, DC-DC Converter, battery charger, power supply of printer, copier, HDD, FDD, TV, VCR, personal computer etc.

MAXIMUM RATINGS (Tc = 25°C)

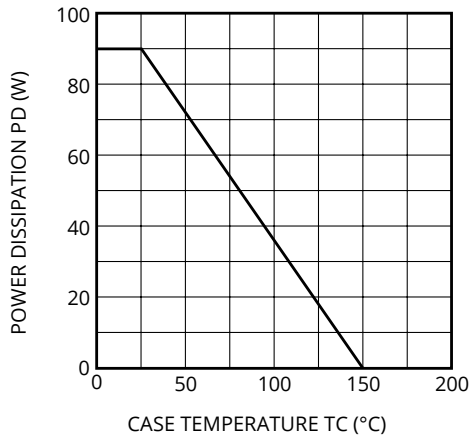
Symbol	Parameter	Conditions	Ratings	Uni
VDSS	Drain-source voltage	VGS = 0V	500	t V
VGSS	Gate-source voltage	VDS = 0V	±30	V
ID	Drain current		5	A
IDM	Drain current (Pulsed)		15	A
PD	Maximum power dissipation		90	W
Tch	Channel temperature		-55 ~ +150	°C
Tstg	Storage temperature		-55 ~ +150	°C
-	Weight	Typical value	2.0	g

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

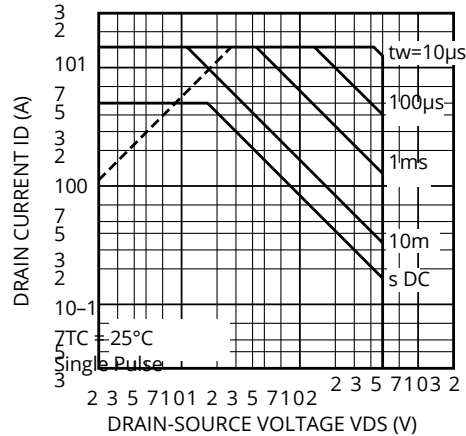
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ.	Max.	
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	—	—	—	V
V _{(BR)GSS}	Gate-source breakdown voltage	I _D = ±100μA, V _{DS} = 0V	500	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25V, V _{DS} = 0V	±30	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 500V, V _{GS} = 0V	—	—	1	mA
V _{GS(th)}	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	—	3	4	V
r _{DS(ON)}	Drain-source on-state resistance	I _D = 2A, V _{GS} = 10V	2	1.4	1.8	Ω
V _{DS(ON)}	Drain-source on-state voltage	I _D = 2A, V _{GS} = 10V	—	2.8	3.6	V
Y _{fs}	Forward transfer admittance	I _D = 2A, V _{DS} = 10V	—	3.0	—	S
C _{iss}	Input capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	1.8	600	—	pF
C _{oss}	Output capacitance		—	80	—	pF
C _{rss}	Reverse transfer capacitance		—	12	—	pF
t _{d(on)}	Turn-on delay time	V _{DD} = 200V, I _D = 2A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	15	—	ns
t _r	Rise time		—	15	—	ns
t _{d(off)}	Turn-off delay time		—	60	—	ns
t _f	Fall time		—	30	—	ns
V _{SD}	Source-drain voltage		I _S = 2A, V _{GS} = 0V	—	1.5	2.0
R _{th(ch-c)}	Thermal resistance	Channel to case	—	—	1.39	°C/W

PERFORMANCE CURVES

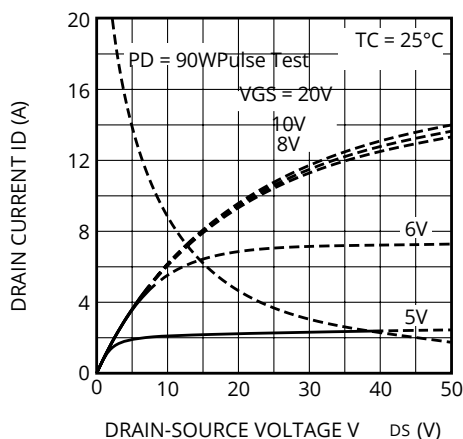
POWER DISSIPATION DERATING CURVE



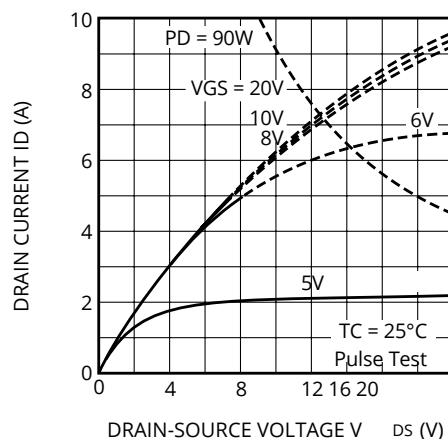
MAXIMUM SAFE OPERATING AREA



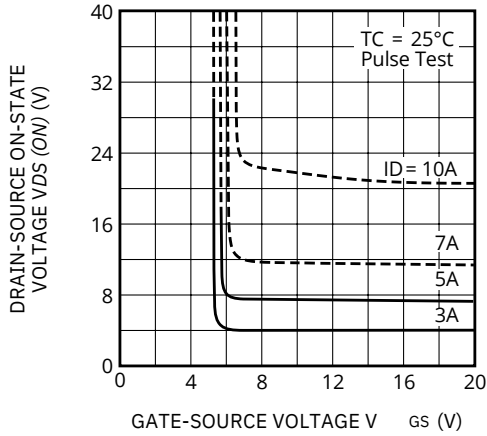
OUTPUT CHARACTERISTICS (TYPICAL)



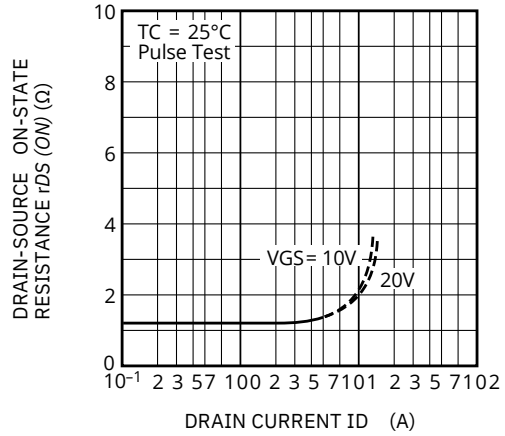
OUTPUT CHARACTERISTICS (TYPICAL)



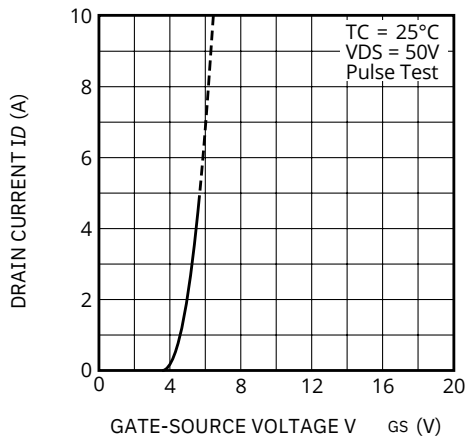
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



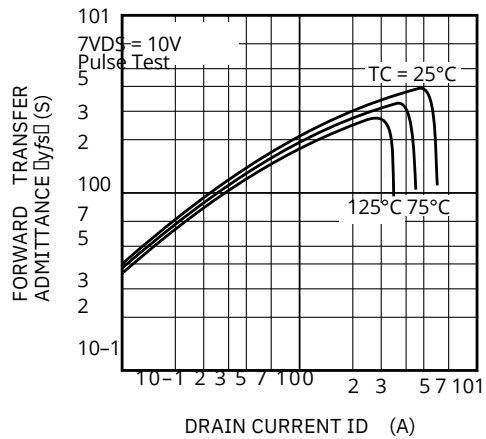
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



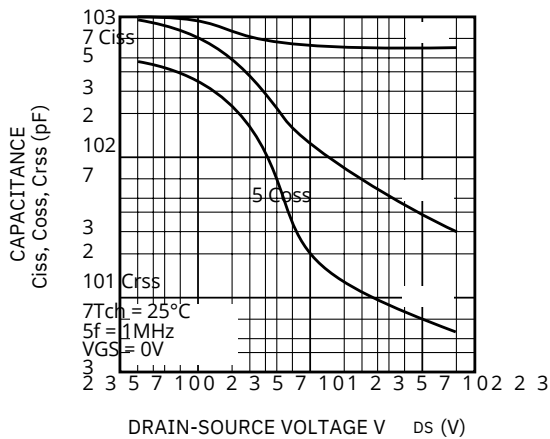
TRANSFER CHARACTERISTICS (TYPICAL)



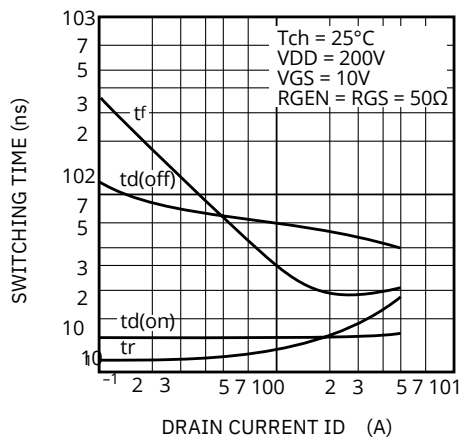
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



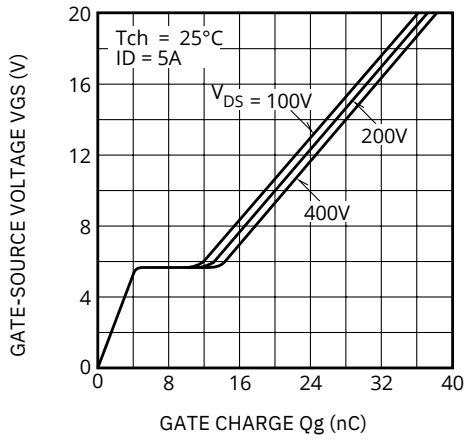
SWITCHING CHARACTERISTICS (TYPICAL)



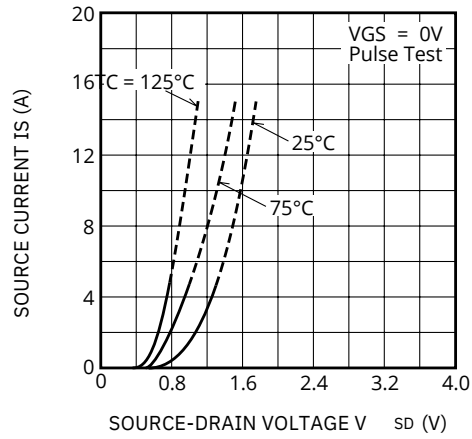
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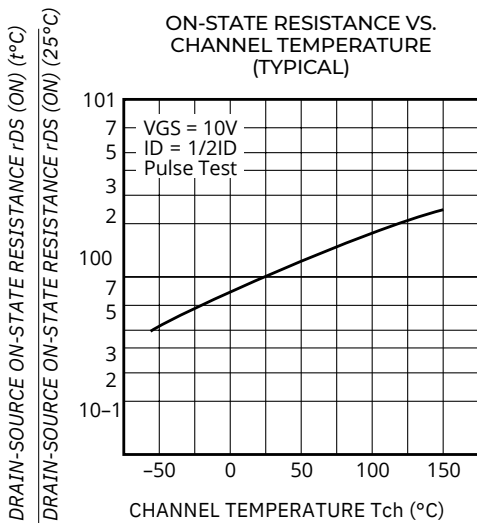
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



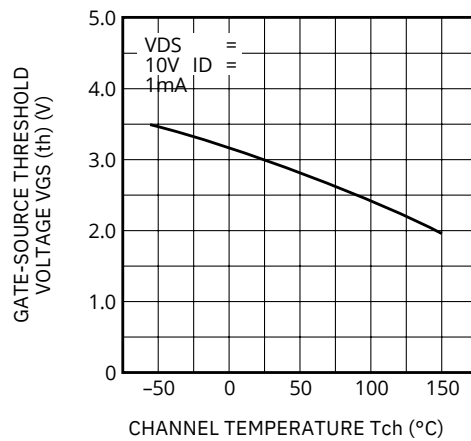
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



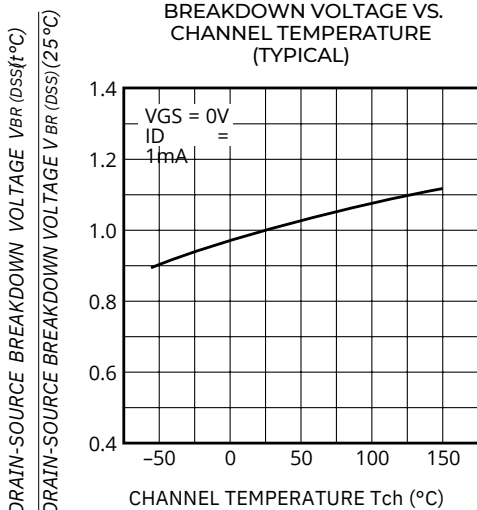
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



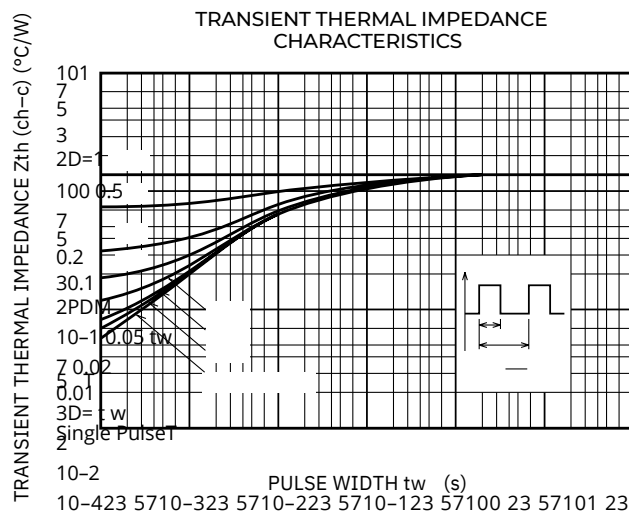
THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



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